

Zener Diode Chips for ESD Protection

1. Feature:

- 1-1 Silicon Zener diode chips for electrostatic discharge(ESD) protection application
- 1-2 This specification applies to P-Type silicon Zener diode chip Device NO:WT-Z106P-4-12

2. Structure:

- 2-1 Planar type: Silicon Diode
- 2-2 Electrodes:
 - Top side:Aluminum Alloy(Anode).
 - Back side:Gold Layer(Cathode).

3. Size:

- 3-1. *Chip size : 6.88 mils x 6.88 mils (175 μ m x 17.5 μ m).
 - 3-2. Chip thickness : 3.3 \pm 0.6 mils (85 \pm 15 μ m).
 - 3-3. Active area : 4.1 mils x 4.1 mils (105 μ m x 105 μ m).
 - 3-4. Bonding pad : 4.5 mils x 4.5 mils (115 μ m x 115 μ m) .
 - 3-5. Pattern drawing : Refer to the attached drawing.
- * Including scribing line. The chip size is about 5.9mil(0.150mm) after dicing.

4. Electrical Characteristics (Ta=25 °C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Zener Voltage	V _Z	I _Z =5mA	11	-	13	V
Forward Voltage	V _f	I _F =20mA	0.75	-	1.2	v
Reverse Leakage Current	I _R	V _R =10V	-	-	100	nA
Electrostatic Discharge	ESD	HBM MIL-STD 883	8.0	-	-	KV

5. Drawing:

